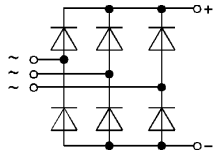
V_{RSM} V_{RRM}	I_D (T_{case} = 100 °C) 110 A	160 A
200 V	**SKD 110/02**	**SKD 160/02**
400 V	**SKD 110/04**	**SKD 160/04**
800 V	**SKD 110/08**	**SKD 160/08**
1200 V	**SKD 110/12**	**SKD 160/12**
1400 V	**SKD 110/14**	**SKD 160/14**
1600 V	**SKD 110/16**	**SKD 160/16**
1800 V	**SKD 110/18***	**SKD 160/18***

Symbol	Conditions	SKD 110	SKD 160	Units
I_D	T_{case} = 100 °C	110	160	A
	T_{amb} = 45 °C, chassis[1)]	28	30	A
	P1/200	70	75	A
	T_{amb} = 35 °C, P1/120 F	110	145	A
	P3/120 F	123	146	A
I_{FSM}	T_{vj} = 25 °C, 10 ms	1200	1800	A
	T_{vj} = 150 °C, 10 ms	1000	1500	A
i^2t	T_{vj} = 25 °C, 8,3...10 ms	7200	16 200	A^2s
	T_{vj} = 150 °C, 8,3...10 ms	5000	11 200	A^2s
V_F	T_{vj} = 25 °C; I_F = 300 A	1, 9	1,65	V
$V_{(TO)}$	T_{vj} = 150 °C	0,85	0,85	V
r_T	T_{vj} = 150 °C	4	3	mΩ
I_{RD}	T_{vj} = 25 °C; V_{RD} = V_{RRM}	0,5	0,5	mA
	T_{vj} = 150 °C; V_{RD} = V_{RRM}	5	6	mA
R_{thjc}	per diode	0,9	0,65	°C/W
	total	0,15	0,11	°C/W
R_{thch}	total	0,03		°C/W
T_{vj}		– 40 . . . + 150		°C
T_{stg}		– 40 . . . + 125		°C
V_{isol}	a.c. 50...60 Hz; r.m.s.; 1 s / 1 min	3600 / 3000		V~
M_1	to heatsink SI units	5 ± 15 %		Nm
	US units	44 ± 15 %		lb. in.
M_2	to terminals SI units	5 ± 15 %		Nm
	US units	44 ± 15 %		lb. in.
w		270		g
Case		G 37		

* Available in limited quantities

SEMIPONT® 4
Power Bridge Rectifiers

SKD 110
SKD 160



SKD

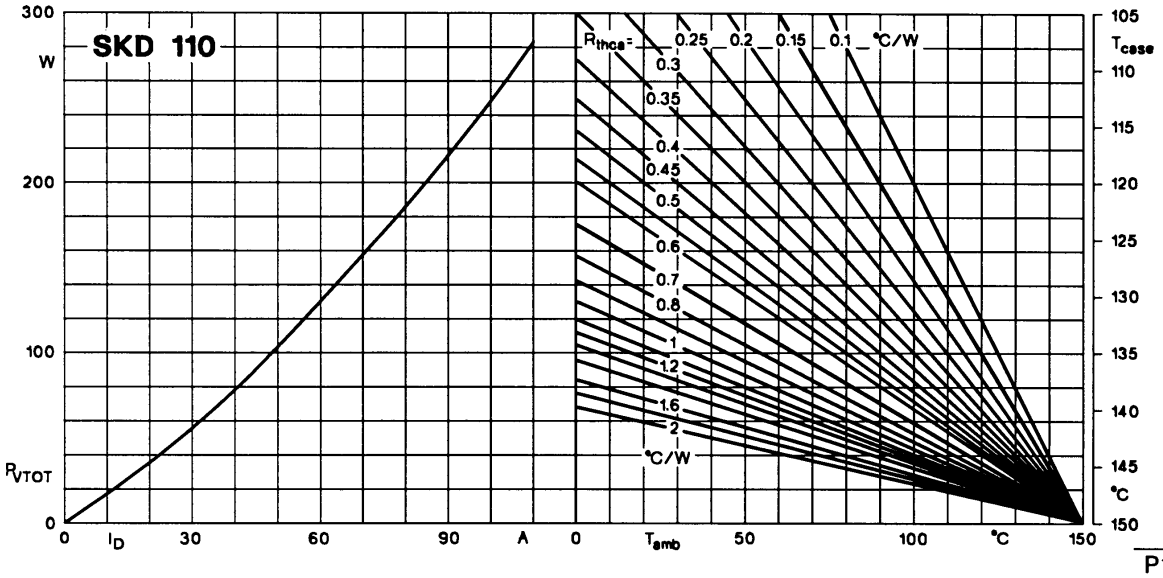
Features

- Robust plastic case with screw terminals
- Large, isolated base plate
- Blocking voltage to 1800 V
- High surge currents
- Easy chassis mounting
- UL recognized, file no. E 63 532

Typical Applications

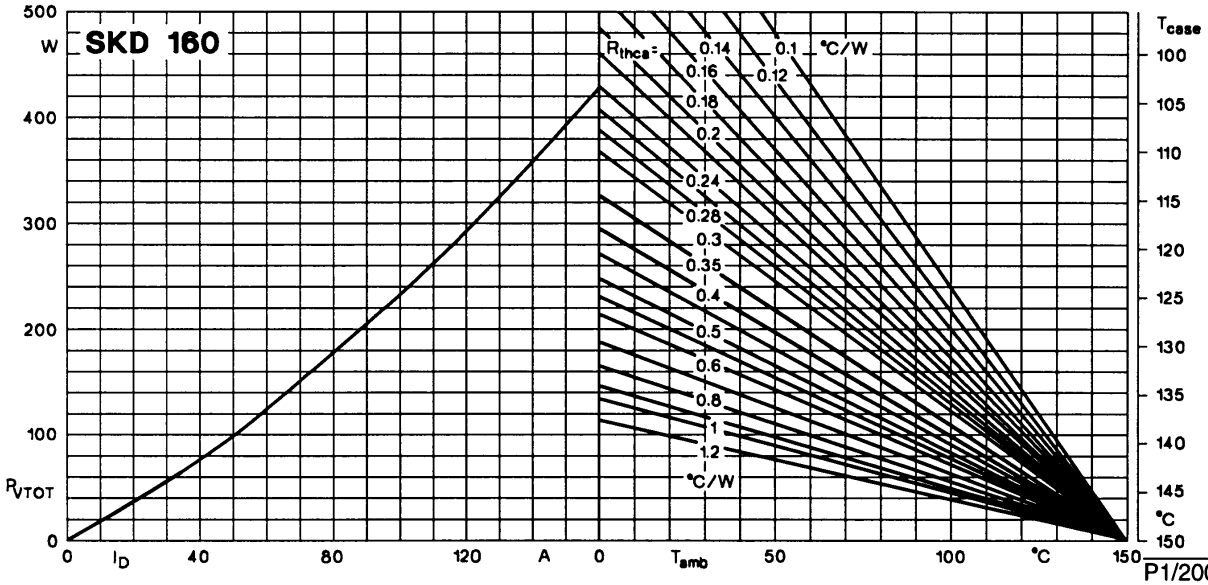
- Three phase rectifiers for power supplies
- Input rectifiers for variable frequency drives
- Rectifiers for DC motor field supplies
- Battery charger rectifiers

[1)] Painted metal sheet of minimum 250 x 250 x 1 mm: R_{thca} = 1,8 °C/W



	R_{thca}
P1/200	0,52 °C/W
P1/120 F	0,20 °C/W

Fig. 3 a Power dissipation vs. output current and case temperature



	R_{thca}
P1/200	0,52 °C/W
P1/120 F	0,20 °C/W

Fig. 3 b Power dissipation vs. output current and case temperature

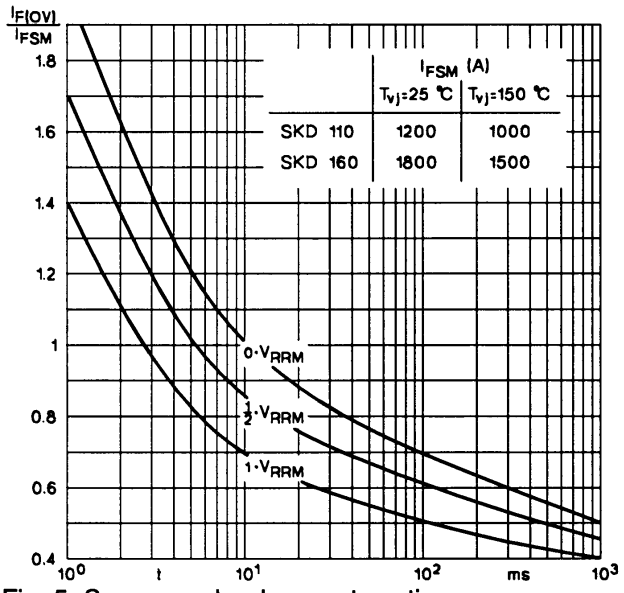


Fig. 5 Surge overload current vs. time

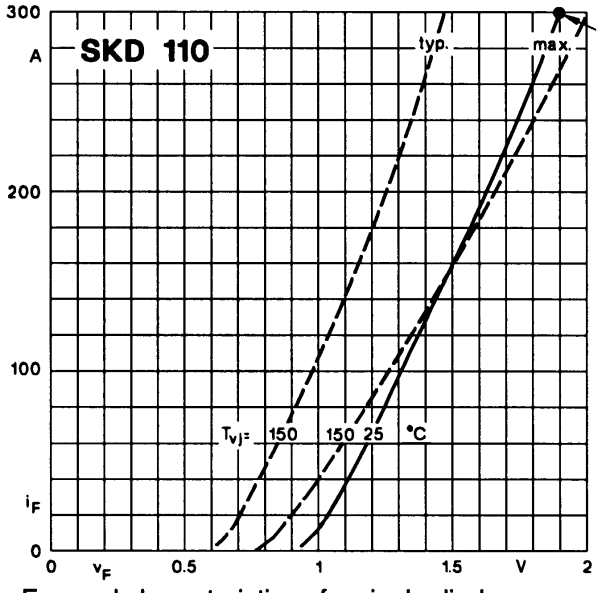


Fig. 9 a Forward characteristics of a single diode

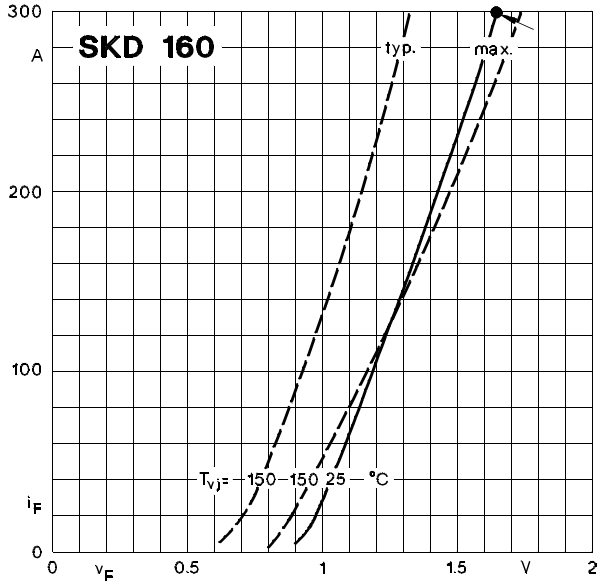


Fig. 9 b Forward characteristics of a single diode

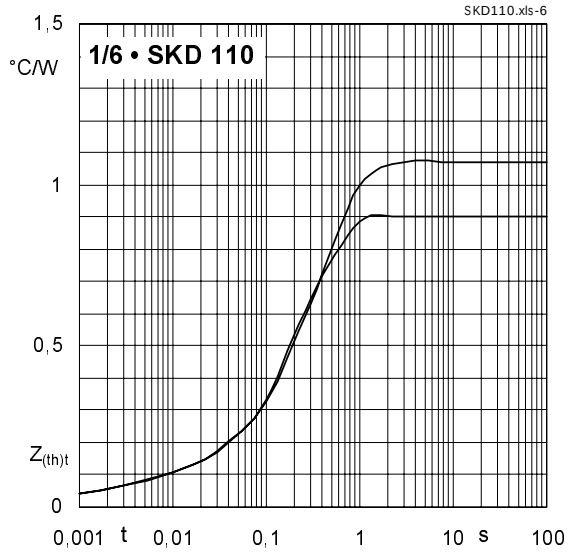


Fig. 12 a Transient thermal impedance vs. time

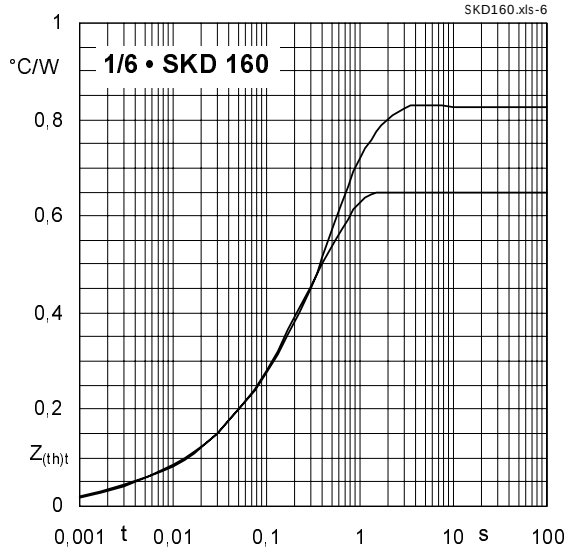
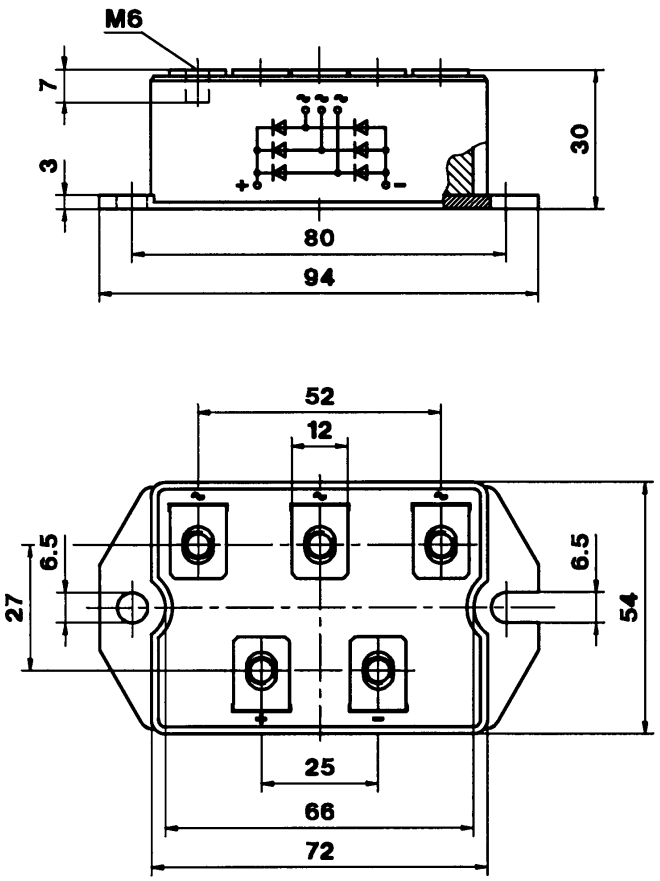


Fig. 12 b Transient thermal impedance vs. time

SKD 110
SKD 160

SEMIPONT® 4

Case G 37



Dimensions in mm